



6N65-C

Preliminary

Power MOSFET

6A, 650V N-CHANNEL POWER MOSFET

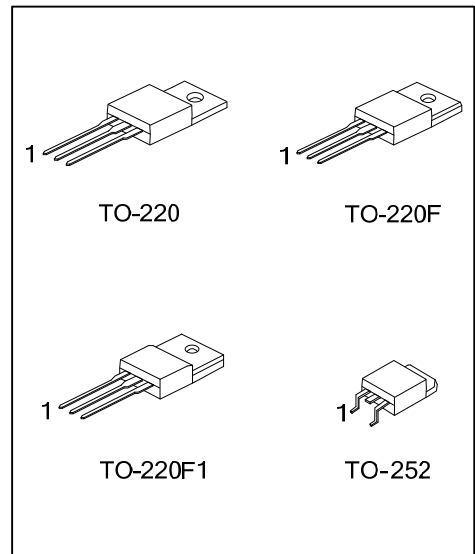
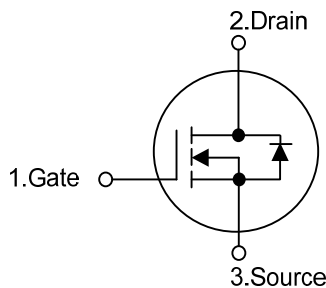
DESCRIPTION

The UTC **6N65-C** is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications of switching power supplies and adaptors.

FEATURES

- * $R_{DS(ON)} < 1.7\Omega$ @ $V_{GS}=10V, I_D=3A$
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness

SYMBOL



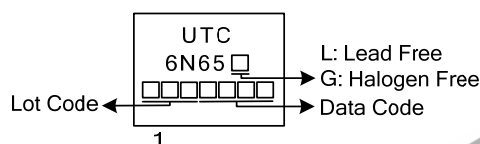
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
6N65L-TA3-T	6N65G-TA3-T	TO-220	G	D	S	Tube
6N65L-TF1-T	6N65G-TF1-T	TO-220F1	G	D	S	Tube
6N65L-TF3-T	6N65G-TF3-T	TO-220F	G	D	S	Tube
6N65L-TN3-R	6N65G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

	<p>(1) T: Tube, R: Tape Reel</p> <p>(2) TA3: TO-220, TF1: TO-220F1, TF3: TO-220F, TN3: TO-252</p> <p>(3) L: Lead Free, G: Halogen Free and Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Avalanche Current (Note 2)		I_{AR}	6	A
Continuous Drain Current		I_D	6	A
Pulsed Drain Current (Note 2)		I_{DM}	24	A
Avalanche Energy (Note 3)	Single Pulsed	E_{AS}	360	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	3	ns
Power Dissipation	TO-220	P_D	120	W
	TO-220F/TO-220F1		40	W
	TO-252		125	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by T_J

3. $L = 20\text{mH}$, $I_{AS} = 6\text{A}$, $V_{DD} = 90\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 6\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL RESISTANCES CHARACTERISTICS

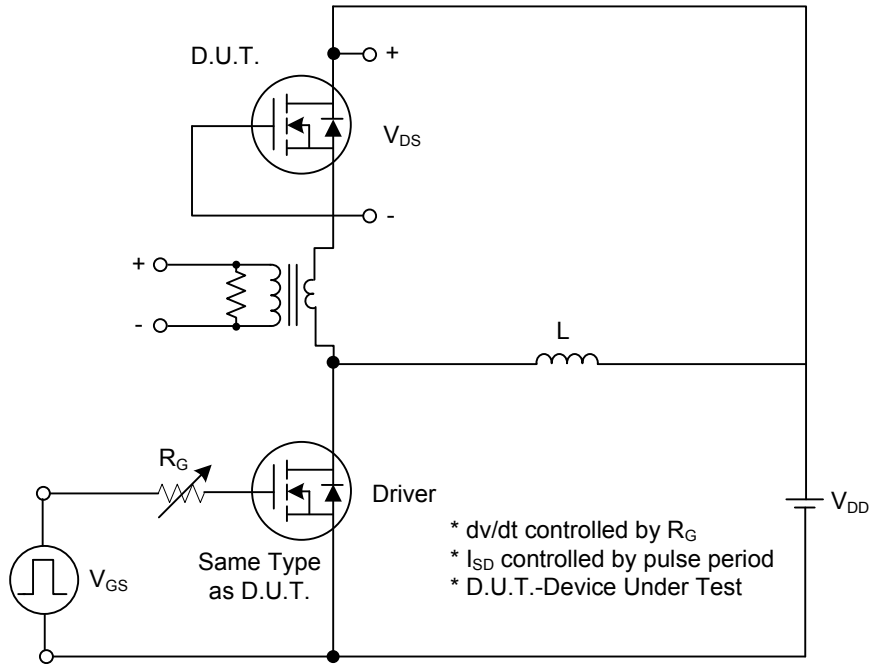
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-252		110	$^\circ\text{C}/\text{W}$
	TO-220		1.04	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220	θ_{JC}	3.2	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1		40	$^\circ\text{C}/\text{W}$
	TO-252			

■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

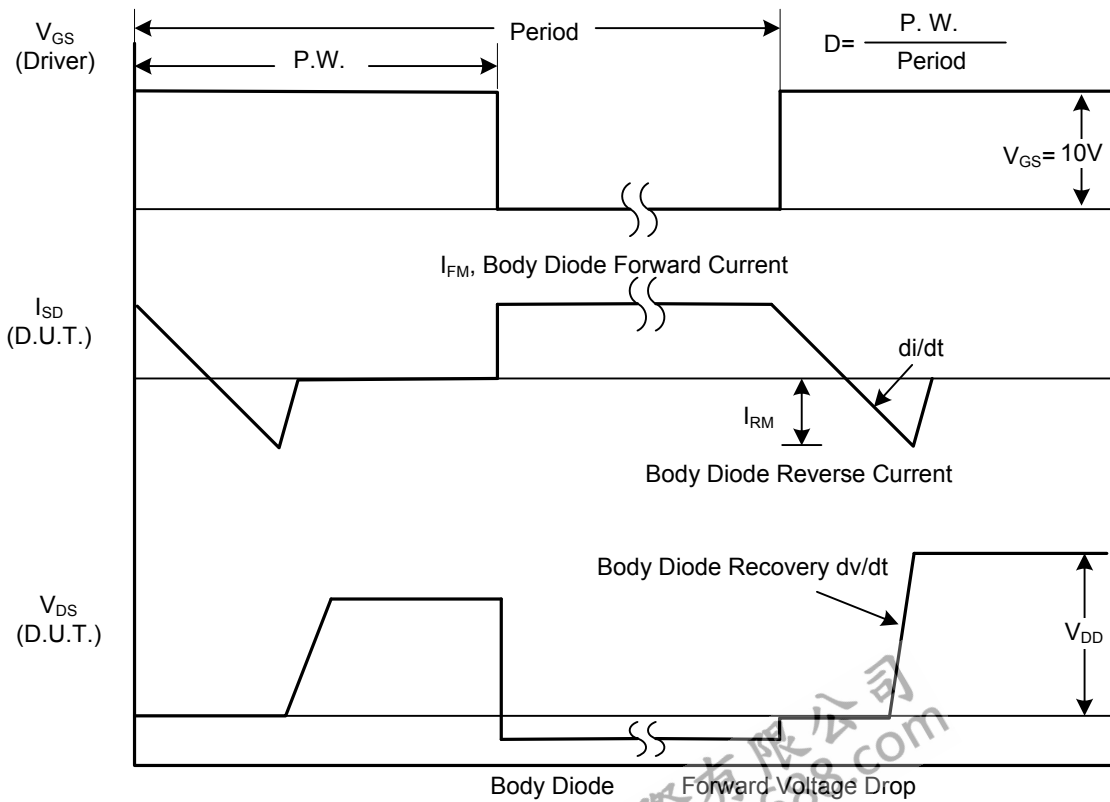
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	650			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=650V, V_{GS}=0V$			10	μA
		$V_{DS}=520V, V_{GS}=0V, T_J=125^\circ C$			100	μA
Gate- Source Leakage Current	Forward	I_{GSS}				nA
	Reverse					
					-100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D=250\mu A$, Referenced to $25^\circ C$		0.53		$V/^\circ C$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=3A$			1.7	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{DS}=25V, V_{GS}=0V, f=1.0\text{ MHz}$		350		pF
Output Capacitance	C_{OSS}			85		pF
Reverse Transfer Capacitance	C_{RSS}			7		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q_G	$V_{DS}=50V, I_D=1.3A, V_{GS}=10V, I_G=100\mu A$ (Note 1, 2)		100		nC
Gate-Source Charge	Q_{GS}			7		nC
Gate-Drain Charge	Q_{GD}			7		nC
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD}=30V, I_D=0.5A, R_G=25\Omega$ (Note 1, 2)		55		ns
Turn-On Rise Time	t_R			40		ns
Turn-Off Delay Time	$t_{D(OFF)}$			215		ns
Turn-Off Fall Time	t_F			45		ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=6A$			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				6	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				24	A
Reverse Recovery Time	t_{RR}	$V_{GS}=0V, I_S=6A,$		340		ns
Reverse Recovery Charge	Q_{RR}	$di_f/dt=100\text{ A}/\mu s$ (Note 1)		3.5		μC

- Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
 2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

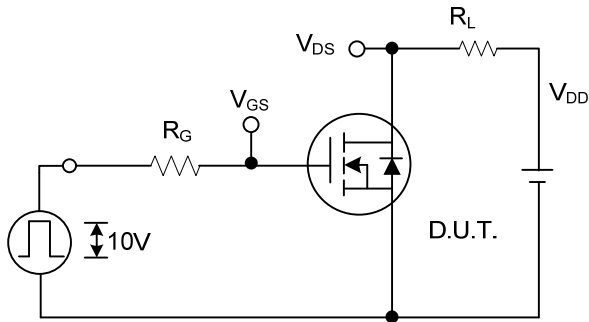


Peak Diode Recovery dv/dt Test Circuit

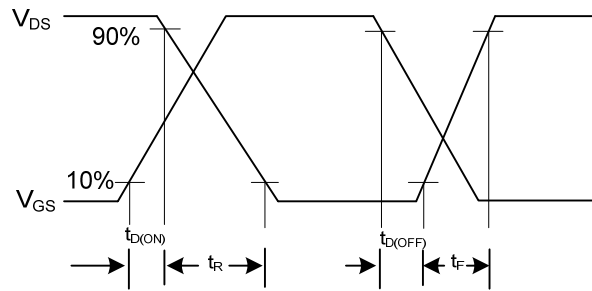


Peak Diode Recovery dv/dt Waveforms

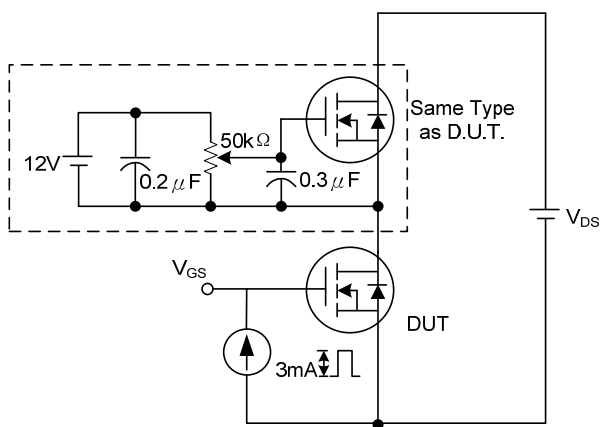
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



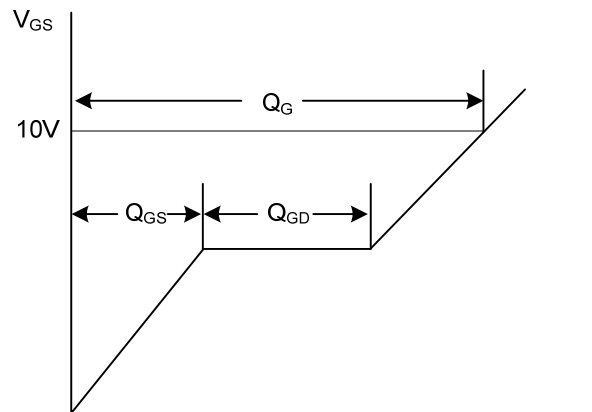
Switching Test Circuit



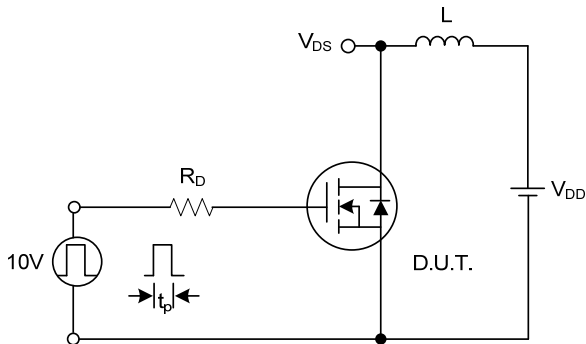
Switching Waveforms



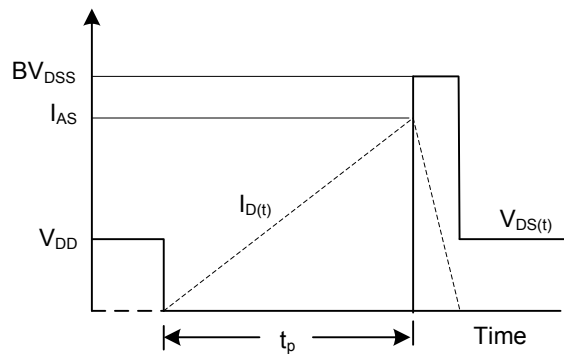
Gate Charge Test Circuit



Charge Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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